# **TO-92 Plastic-Encapsulate Transistors**

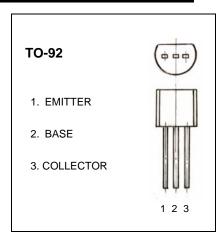
2N2222A TRANSISTOR (NPN)

#### **FEATURE**

Complementary NPN Type available (MPS2222)

### MAXIMUM RATINGS (T<sub>A</sub>=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	75 V		
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
Ic	Collector Current -Continuous	600	mA	
Pc	Collector Power Dissipation 625 n		mW	
TJ	Junction Temperature 150 ℃		°C	
T <sub>stg</sub>	Storage Temperature	-55-150	°C	



## **ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10uA , I <sub>E</sub> =0	75		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 10mA , I <sub>B</sub> =0	40		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10uA, I <sub>C</sub> =0	6		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 60V, I <sub>E</sub> =0		10	nA
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> = 60V,V <sub>EB(Off)</sub> =3V		10	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 3 V, I <sub>C</sub> =0		100	nA
	h <sub>FE(1)</sub>	V <sub>CE</sub> =10V,I <sub>C</sub> = 150mA	100	300	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> =10V,I <sub>C</sub> = 0.1mA	40		
	h <sub>FE(3)</sub> *	V <sub>CE</sub> =10V, I <sub>C</sub> = 500mA	42		
Collector-emitter saturation voltage	V <sub>CE(sat)(1)</sub> *	I <sub>C</sub> = 500mA, I <sub>B</sub> =50mA		0.6	V
Conector-enlitter saturation voltage	V <sub>CE(sat)(2)</sub> *	I <sub>C</sub> = 150mA, I <sub>B</sub> =15mA		0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub> *	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA		1.2	V
Delay time		V <sub>CC</sub> =30V, V <sub>EB(Off)</sub> =-0.5V,		10	nS
Rise time	t <sub>r</sub>	I <sub>C</sub> =150mA,I <sub>B1</sub> =15mA		25	nS
Storage time	ts	V <sub>CC</sub> =30V,Ic=150mA,I <sub>B1</sub> =I <sub>B2</sub> =15mA		225	nS
Fall time	t <sub>f</sub>	VCC=50V,IC=150HIA,IB1=IB2=15HIA		60	nS
Transition frequency	f⊤	V <sub>CE</sub> =20V, I <sub>C</sub> =20mA, f=100MHz	300		MHz

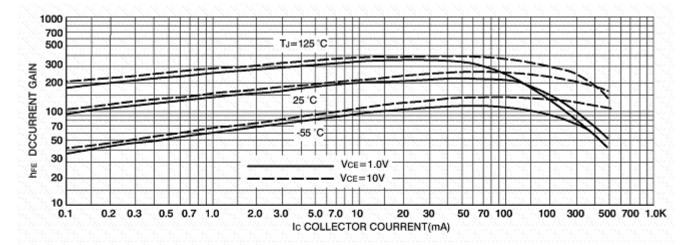
\*pulse test

#### CLASSIFICATION OF h<sub>FE(1)</sub>

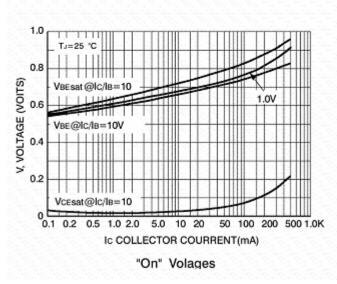
Rank	L	Н
Range	100-200	200-300

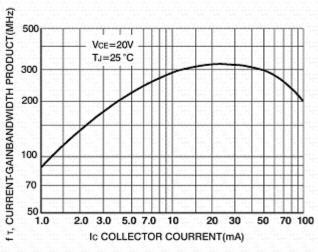
## **Typical Characteristics**

### **MPS2222A**



DC Current Gain





Current-Gain Bandwidth Product